



**2SB1133**

**PNP EPITAXIAL SILICON TRANSISTOR**

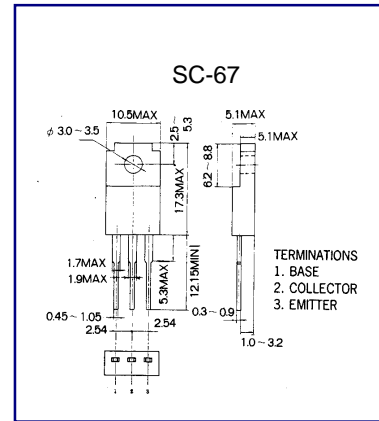
**POWER AMPLIFIER**

**VERTICAL DEFLECTION OUTPUT**



**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base voltage	V <sub>EB0</sub>	-5	V
Collector Current (DC)	I <sub>C</sub>	-3	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>C</sub>	20	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-50~150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = -150V , I <sub>E</sub> =0			-10	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = -5V , I <sub>C</sub> =0			-10	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = -2.0V , I <sub>C</sub> =-1.0A	70		240	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-3A , I <sub>B</sub> =-0.3mA			-1.4	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -10V , I <sub>C</sub> =-0.5A		60		MHZ